Paul koenraad

List of Publications by Year
in descending order

228 papers	5,736 citations	76326 40 h-index	110387 64 g-index
232 all docs	232 docs citations	232 times ranked	4719 citing authors

#	Article	IF	Citations
1	Single dopants in semiconductors. Nature Materials, 2011, 10, 91-100.	27.5	385
2	Determination of the shape and indium distribution of low-growth-rate InAs quantum dots by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2002, 81, 1708-1710.	3.3	200
3	Oscillatory Persistent Currents in Self-Assembled Quantum Rings. Physical Review Letters, 2007, 99, 146808.	7.8	192
4	Spatial Structure of an Individual Mn Acceptor in GaAs. Physical Review Letters, 2004, 92, 216806.	7.8	185
5	Controlled Charge Switching on a Single Donor with a Scanning Tunneling Microscope. Physical Review Letters, 2008, 101, 076103.	7.8	150
6	Atomic-scale structure of self-assembled In(Ga)As quantum rings in GaAs. Applied Physics Letters, 2005, 87, 131902.	3.3	126
7	Strong Carrierâ€“Phonon Coupling in Lead Halide Perovskite Nanocrystals. ACS Nano, 2017, 11, 11024-11030.	14.6	119
8	Capping process of InAsâˆ•GaAs quantum dots studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2004, 85, 5697-5699.	3.3	103
9	Temperature-dependent membrane fatty acid and cell physiology changes in coccoid forms of Campylobacter jejuni. Applied and Environmental Microbiology, 1995, 61, 2713-2719.	3.1	95
10	Theory of electron energy spectrum and Aharonov-Bohm effect in self-assembled<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>âˆ'</mml:mo><mml:mi>x</mml:mi></mml:mrow>< mathvariant="normal">As</mml:mi></mml:mrow></mml:math>quantum rings in GaAs. Physical Review B, 2007, 76, .	3.2	90
11	GaAsSb-capped InAs quantum dots: From enlarged quantum dot height to alloy fluctuations. Physical Review B, 2010, 81, .	3.2	86
12	Suppression of InAsâˆ•GaAs quantum dot decomposition by the incorporation of a GaAsSb capping layer. Applied Physics Letters, 2007, 90, 213105.	3.3	85
13	Growth and Optical Properties of Direct Band Gap Ge/Ge_{0.87}Sn_{0.13} Core/Shell Nanowire Arrays. Nano Letters, 2017, 17, 1538-1544.	9.1	72
14	Atomic-scale structure and photoluminescence of InAs quantum dots in GaAs and AlAs. Physical Review B, 2005, 72, .	3.2	71
15	Electronic and optical properties ofInAsâˆ•InPquantum dots on InP(100) andInP(311)Bsubstrates: Theory and experiment. Physical Review B, 2006, 74, .	3.2	67
16	Warping a single Mn acceptor wavefunction by straining the GaAs host. Nature Materials, 2007, 6, 512-515.	27.5	65
17	Observation of high mobility and cyclotron resonance in 20 Å… silicon delta-doped GaAs grown by MBE at 480 Â°C. Semiconductor Science and Technology, 1990, 5, 861-866.	2.0	60
18	Atomic scale analysis of self assembled GaAs/AlGaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2010, 96, .	3.3	60

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19	Formation of InAs wetting layers studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2005, 87, 111903.	3.3	57
20	Enhanced Donor Binding Energy Close to a Semiconductor Surface. Physical Review Letters, 2009, 102, 166101.	7.8	57
21	In vitrosusceptibility of campylobacter and salmonella isolates from broilers to quinolones, ampicillin, tetracycline, and erythromycin. Veterinary Quarterly, 1994, 16, 206-208.	6.7	55
22	Stacked low-growth-rate InAs quantum dots studied at the atomic level by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2003, 82, 3758-3760.	3.3	55
23	Ellipsoidal InAs quantum dots observed by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2009, 94, 023107.	3.3	53
24	Many-body exciton states in self-assembled quantum dots coupled to a Fermi sea. Nature Physics, 2010, 6, 534-538.	16.7	52
25	Smooth and Selfâ€Similar SiO₂â€like Films on Polymers Synthesized in Rollâ€toâ€Roll Atmospheric Pressureâ€PECVD for Gas Diffusion Barrier Applications. Plasma Processes and Polymers, 2010, 7, 635-639.	3.0	51
26	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>g</mml:mi></mml:math>factors and diamagnetic coefficients of electrons, holes, and excitons in InAs/InP quantum dots. Physical Review B, 2012, 85, .	3.2	51
27	Boosting Hole Mobility in Coherently Strained [110]-Oriented Geâ€“Si Coreâ€“Shell Nanowires. Nano Letters, 2017, 17, 2259-2264.	9.1	51
28	Direct Probing of the Dielectric Scavenging-Layer Interface in Oxide Filamentary-Based Valence Change Memory. ACS Applied Materials & Interfaces, 2017, 9, 10820-10824.	8.0	50
29	Tunneling spectroscopy across GaAs/AlxGa1âˆ’xAs interfaces at nanometer resolution. Physical Review B, 1992, 45, 6946-6949.	3.2	49
30	Relating Substitution to Single-Chain Conformation and Aggregation in Poly(p-phenylene Vinylene) Films. Nano Letters, 2003, 3, 1191-1196.	9.1	49
31	Atomic scale study of the impact of the strain and composition of the capping layer on the formation of InAs quantum dots. Journal of Applied Physics, 2007, 101, 081707.	2.5	48
32	High Quality SiO₂â€like Layers by Large Area Atmospheric Pressure Plasma Enhanced CVD: Deposition Process Studies by Surface Analysis. Plasma Processes and Polymers, 2009, 6, 693-702.	3.0	46
33	Composition profiling of InAs quantum dots and wetting layers by atom probe tomography and cross-sectional scanning tunneling microscopy. Physical Review B, 2011, 83, .	3.2	46
34	Be Delta-Doped Layers in GaAs Imaged with Atomic Resolution Using Scanning Tunneling Microscopy. Physical Review Letters, 1995, 75, 1606-1609.	7.8	45
35	Formation of columnar (In,Ga)As quantum dots on GaAs(100). Applied Physics Letters, 2004, 85, 2771-2773.	3.3	45
36	Structure of quantum dots as seen by excitonic spectroscopy versus structural characterization: Using theory to close the loop. Physical Review B, 2009, 80, .	3.2	45

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37	Interplay between tip-induced band bending and voltage-dependent surface corrugation on GaAs(110) surfaces. Physical Review B, 2002, 66, .	3.2	44
38	The structural, electronic and optical properties of GaSb/GaAs nanostructures for charge-based memory. Journal Physics D: Applied Physics, 2013, 46, 264001.	2.8	44
39	Atomically precise impurity identification and modification on the manganese doped GaAs(110) surface with scanning tunneling microscopy. Physical Review B, 2008, 78, .	3.2	42
40	Role of segregation in InAs/GaAs quantum dot structures capped with a GaAsSb strain-reduction layer. Physical Review B, 2009, 80, .	3.2	41
41	Optical observation of single-carrier charging in type-II quantum ring ensembles. Applied Physics Letters, 2012, 100, .	3.3	41
42	GaSb/GaAs quantum dot formation and demolition studied with cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2012, 100, .	3.3	40
43	Intersubbandâ€coupling and screening effects on the electron transport in a quasiâ€twoâ€dimensional Î´â€doped semiconductor system. Journal of Applied Physics, 1996, 80, 5809-5814.	2.5	38
44	Scanning tunneling spectroscopy on organic semiconductors: Experiment and model. Physical Review B, 2004, 70, .	3.2	38
45	Spatial Structure of Mn-Mn Acceptor Pairs in GaAs. Physical Review Letters, 2005, 95, 256402.	7.8	38
46	The speciation and subtyping of campylobacter isolates from sewage plants and waste water from a connected poultry abattoir using molecular techniques. Epidemiology and Infection, 1995, 115, 485-494.	2.1	37
47	Relaxation of a strained quantum well at a cleaved surface. Journal of Applied Physics, 2002, 91, 4171-4176.	2.5	37
48	Suppressing Segregation in Highly Phosphorus Doped Silicon Monolayers. ACS Nano, 2015, 9, 12537-12541.	14.6	36
49	Pâ€"N Junctions in Ultrathin Topological Insulator Sb₂Te₃/Bi₂Te₃ Heterostructures Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2016, 16, 2057-2061.	3.0	36
50	Linking structural and electronic properties of high-purity self-assembled GaSb/GaAs quantum dots. Physical Review B, 2012, 86, .	3.2	35
51	Atom-by-Atom Analysis of Semiconductor Nanowires with Parts Per Million Sensitivity. Nano Letters, 2017, 17, 599-605.	9.1	35
52	Energy spectra and oscillatory magnetization of two-electron self-assembled<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> rings in GaAs. Physical Review B, 2008, 77, .	3.2	34
53	Observation and explanation of strong electrically tunable exciton<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>g</mml:mi></mml:mrow></mml:math>factors in composition engineered In(Ga)As quantum dots. Physical Review B, 2011, 83, .	3.2	34
54	Precise shape engineering of epitaxial quantum dots by growth kinetics. Physical Review B, 2015, 92, .	3.2	34

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55	Optical study of the band structure of wurtzite GaP nanowires. Journal of Applied Physics, 2016, 120, .	2.5	34
56	High-purity 3D nano-objects grown by focused-electron-beam induced deposition. Nanotechnology, 2016, 27, 355301.	2.6	34
57	FrÃ¶hlich interaction dominated by a single phonon mode in CsPbBr3. Nature Communications, 2021, 12, 5844.	12.8	34
58	Use of the Schiller decapitation process for the manufacture of high quality tungsten scanning tunneling microscopy tips. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1946.	1.6	33
59	Excitonic behavior in self-assembled InAs/GaAs quantum rings in high magnetic fields. Physical Review B, 2009, 80, .	3.2	33
60	Analysis of the modified optical properties and band structure of GaAs1âˆ’xSbx-capped InAs/GaAs quantum dots. Journal of Applied Physics, 2012, 112, .	2.5	33
61	Size-dependent line broadening in the emission spectra of single GaAs quantum dots: Impact of surface charge on spectral diffusion. Physical Review B, 2015, 92, .	3.2	33
62	Enhanced phonon-assisted photoluminescence in InAs/GaAs parallelepiped quantum dots. Physical Review B, 2000, 61, R2436-R2439.	3.2	30
63	Size-dependent exciton<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>g</mml:mi></mml:math>factor in self-assembled InAs/InP quantum dots. Physical Review B, 2009, 79, .	3.2	30
64	Exchange-correlation energy of a hole gas including valence band coupling. Physical Review B, 1997, 56, 3664-3671.	3.2	29
65	Single-exciton spectroscopy of single Mn doped InAs quantum dots. Physical Review B, 2008, 78, .	3.2	29
66	Digital alloy interface grading of an InAlAs/InGaAs quantum cascade laser structure studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2003, 83, 4131-4133.	3.3	28
67	Surface Induced Asymmetry of Acceptor Wave Functions. Physical Review Letters, 2010, 104, 086404.	7.8	28
68	An atomic scale study on the effect of Sb during capping of MBE grown IIIâ€“V semiconductor QDs. Semiconductor Science and Technology, 2011, 26, 064007.	2.0	28
69	InAs quantum dot morphology after capping with In, N, Sb alloyed thin films. Applied Physics Letters, 2014, 104, .	3.3	28
70	Subband population and electron subband mobility for two interacting Si-Î´-doping layers in GaAs. Physica B: Condensed Matter, 1993, 184, 221-225.	2.7	27
71	Atomic-scale structure and formation of self-assembled In(Ga)As quantum rings. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 41-45.	2.7	27
72	Formation of InAs quantum dots and wetting layers in GaAs and AlAs analyzed by cross-sectional scanning tunneling microscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 236-240.	2.7	26

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73	Enhanced binding energy of manganese acceptors close to the GaAs(110) surface. Physical Review B, 2010, 82, .	3.2	26
74	The disintegration of GaSb/GaAs nanostructures upon capping. Applied Physics Letters, 2013, 102, .	3.3	26
75	Size and shape tunability of self-assembled InAs/GaAs nanostructures through the capping rate. Applied Surface Science, 2018, 444, 260-266.	6.1	26
76	Anisotropy of electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>tensors of quantum dots: An intuitive picture based on spin-correlated orbital currents. Physical Review B, 2016, 93, .	3.2	25
77	Capping of InAs quantum dots grown on (311)B InP studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2006, 89, 023119.	3.3	24
78	Single Si dopants in GaAs studied by scanning tunneling microscopy and spectroscopy. Physical Review B, 2011, 84, .	3.2	24
79	Highly nonlinear excitonic Zeeman spin splitting in composition-engineered artificial atoms. Physical Review B, 2012, 85, .	3.2	24
80	Blueshifts of the emission energy in type-II quantum dot and quantum ring nanostructures. Journal of Applied Physics, 2013, 114, 073519.	2.5	24
81	Antibiotic susceptibility of campylobacter isolates from sewage and poultry abattoir drain water. Epidemiology and Infection, 1995, 115, 475-483.	2.1	23
82	High-field magnetotransport in a two-dimensional electron gas in quantizing magnetic fields and intense terahertz laser fields. Journal of Physics Condensed Matter, 2004, 16, 89-101.	1.8	23
83	Double capping of molecular beam epitaxy grown InAsâˆ•InP quantum dots studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2007, 91, .	3.3	23
84	Quantum- and transport electron mobility in the individual subbands of a two-dimensional electron gas in Si-Î´-doped GaAs. Physica B: Condensed Matter, 1992, 177, 485-490.	2.7	22
85	Evidence for strain in and around InAs quantum dots in GaAs from ion-channeling experiments. Physical Review B, 2000, 61, 8270-8275.	3.2	22
86	Anisotropic spatial structure of deep acceptor states in GaAs and GaP. Physical Review B, 2008, 77, .	3.2	21
87	Determination of the outward relaxation of cleaved strained InAs structures by scanning tunneling microscopy. Applied Surface Science, 2002, 190, 258-263.	6.1	20
88	Structural properties of GaAsNâˆ•GaAs quantum wells studied at the atomic scale by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2008, 93, 083103.	3.3	20
89	Spin-Orbit-Induced Circulating Currents in a Semiconductor Nanostructure. Physical Review Letters, 2014, 112, 187201.	7.8	20
90	Atomic-Scale Characterization of Droplet Epitaxy Quantum Dots. Nanomaterials, 2021, 11, 85.	4.1	20

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91	Optical Detection of Ballistic Electrons Injected by a Scanning-Tunneling Microscope. Physical Review Letters, 2001, 86, 2404-2407.	7.8	19
92	Influence of an ultrathin GaAs interlayer on the structural properties of InAsâˆ•InGaAsPâˆ•InP (001) quantum dots investigated by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2008, 92, 083103.	3.3	19
93	Bistable behavior of silicon atoms in the (110) surface of gallium arsenide. Physical Review B, 2011, 84, .	3.2	19
94	Electron and exciton energy spectra in selfâ€assembled InGaAs/GaAs ringâ€like nanostructures. Physica Status Solidi (B): Basic Research, 2008, 245, 2657-2661.	1.5	18
95	Core-state manipulation of single Fe impurities in GaAs with a scanning tunneling microscope. Physical Review B, 2013, 87, .	3.2	18
96	Noise due to localized states in the quantum hall regime. Solid State Communications, 1986, 60, 831-834.	1.9	17
97	Micro and Nanoscale Characterization of Complex Multilayer-Structured White Etching Layer in Rails. Metals, 2018, 8, 749.	2.3	17
98	Te incorporation and activation as <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type dopant in self-catalyzed GaAs nanowires. Physical Review Materials, 2019, 3, .	2.4	17
99	Photoluminescence study of Si delta-doped GaAs. Semiconductor Science and Technology, 1991, 6, 1079-1087.	2.0	15
100	Simple and efficient scanning tunneling luminescence detection at low-temperature. Review of Scientific Instruments, 2009, 80, 123704.	1.3	15
101	The role of dot height in determining exciton lifetimes in shallow InAs/GaAs quantum dots. Applied Physics Letters, 2010, 96, .	3.3	15
102	An atomically resolved study of InGaAs quantum dot layers grown with an indium flush step. Nanotechnology, 2010, 21, 215705.	2.6	15
103	Surface Dynamics of SiO₂â€like Films on Polymers Grown by DBD Assisted CVD at Atmospheric Pressure. Plasma Processes and Polymers, 2012, 9, 1194-1207.	3.0	15
104	Strain-induced<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>-factor tuning in single InGaAs/GaAs quantum dots. Physical Review B, 2016, 94, .	3.2	15
105	Analysis of the shallow and deep center occupancies in Siâ€doped AlxGa1âˆ’xAs using a multilevel donor model. Journal of Applied Physics, 1989, 66, 4269-4274.	2.5	14
106	Electron mobility in Si Î´-doped GaAs with spatial correlationsin the distribution of charged impurities. Physical Review B, 1997, 55, 13093-13099.	3.2	14
107	Spectrally resolved luminescence from an InGaAs quantum well induced by an ambient scanning tunneling microscope. Applied Physics Letters, 1999, 75, 3656-3658.	3.3	14
108	Low-temperature scanning-tunneling microscope for luminescence measurements in high magnetic fields. Review of Scientific Instruments, 2001, 72, 132-135.	1.3	14

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109	Control of polarization and dipole moment in low-dimensional semiconductor nanostructures. Applied Physics Letters, 2009, 95, 221116.	3.3	14
110	Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots. Physical Review B, 2010, 82, .	3.2	14
111	Bistable Charge Configuration of Donor Systems near the GaAs(110) Surfaces. Nano Letters, 2011, 11, 3538-3542.	9.1	14
112	Structural atomic-scale analysis of GaAs/AlGaAs quantum wires and quantum dots grown by droplet epitaxy on a (311)A substrate. Applied Physics Letters, 2011, 98, 193112.	3.3	14
113	Atomically resolved study of the morphology change of InAs/GaAs quantum dot layers induced by rapid thermal annealing. Applied Physics Letters, 2012, 101, .	3.3	14
114	Structural and compositional analysis of (InGa)(AsSb)/GaAs/GaP Stranskiâ€“Krastanov quantum dots. Light: Science and Applications, 2021, 10, 125.	16.6	14
115	Cross-sectional scanning tunneling microscopy of InAs/GaAs(001) submonolayer quantum dots. Physical Review Materials, 2020, 4, .	2.4	14
116	Shift of the DX level in narrow Si delta-doped GaAs. Semiconductor Science and Technology, 1991, 6, B143-B145.	2.0	13
117	Random electric fields and impurity diffusion inÎ´layers. Physical Review B, 2000, 61, 3033-3038.	3.2	13
118	Excited states of ring-shaped (InGa)As quantum dots in aGaAsâˆ•(AlGa)Asquantum well. Physical Review B, 2005, 72, .	3.2	13
119	Shape control of quantum dots studied by cross-sectional scanning tunneling microscopy. Journal of Applied Physics, 2011, 109, 102413.	2.5	13
120	Morphological Description of Ultraâ€Smooth Organoâ€Silicone Layers Synthesized Using Atmospheric Pressure Dielectric Barrier Discharge Assisted PECVD. Plasma Processes and Polymers, 2013, 10, 313-319.	3.0	13
121	Composition profiling of GaAs/AlGaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2014, 105, .	3.3	13
122	1/f noise in Î´-doped GaAs analyzed in terms of mobility fluctuations. Physical Review B, 1997, 55, 5290-5296.	3.2	12
123	STM observations of GaAs(110) showing the top and bottom zig-zag rows of the surface. Physical Review B, 2001, 64, .	3.2	12
124	Real-Space Measurement of the Potential Distribution Inside Organic Semiconductors. Physical Review Letters, 2002, 88, 096803.	7.8	12
125	Kinetic Monte Carlo simulations and cross-sectional scanning tunneling microscopy as tools to investigate the heteroepitaxial capping of self-assembled quantum dots. Physical Review B, 2012, 85, .	3.2	12
126	Highly Tensile-Strained Self-Assembled Ge Quantum Dots on InP Substrates for Integrated Light Sources. ACS Applied Nano Materials, 2021, 4, 897-906.	5.0	12

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127	Magneto-optical study on exciton screening inp-typeAlxGa1âxAs/InyGa1âyAsquantum wells. Physical Review B, 1997, 56, 4853-4862.	3.2	11
128	Composition profiling at the atomic scale in IIIâ€"V nanostructures by cross-sectional STM. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 526-532.	2.7	11
129	Generalized effective-mass theory of subsurface scanning tunneling microscopy: Application to cleaved quantum dots. Physical Review B, 2010, 82, .	3.2	11
130	Influence of the tip work function on scanning tunneling microscopy and spectroscopy on zinc doped GaAs. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 1086-1092.	1.2	11
131	Scanning tunneling microscopy reveals LiMnAs is a room temperature anti-ferromagnetic semiconductor. Applied Physics Letters, 2012, 100, 112107.	3.3	11
132	Incorporation of Bi atoms in InP studied at the atomic scale by cross-sectional scanning tunneling microscopy. Physical Review Materials, 2017, 1, .	2.4	11
133	Spatially resolved scanning tunneling luminescence on self-assembled InGaAs/GaAs quantum dots. Applied Physics Letters, 2003, 83, 290-292.	3.3	10
134	Observation of cyclotron resonance in an InAs/GaAs wetting layer with shallowly formed quantum dots. Physical Review B, 2003, 68, .	3.2	10
135	Effect of a lattice-matched GaAsSb capping layer on the structural properties of InAs/InGaAs/InP quantum dots. Journal of Applied Physics, 2010, 107, .	2.5	10
136	Atomic scale characterization of Mn doped InAs/GaAs quantum dots. Applied Physics Letters, 2010, 96, .	3.3	10
137	Bulk AlInAs on InP(111) as a novel material system for pure single photon emission. Optics Express, 2016, 24, 23198.	3.4	10
138	Electronic wave functions and optical transitions in (In,Ga)As/GaP quantum dots. Physical Review B, 2016, 94, .	3.2	10
139	Scanning tunneling microscopy contrast of isovalent impurities on the GaAs (110) surface explained with a geometrical model. Physical Review B, 2016, 93, .	3.2	10
140	Influence of growth conditions on the performance of InP nanowire solar cells. Nanotechnology, 2016, 27, 454003.	2.6	10
141	Composition analysis and transition energies of ultrathin Sn-rich GeSn quantum wells. Physical Review Materials, 2020, 4, .	2.4	10
142	Effect of strain on a second-order van Hove singularity inAlxGa1â^'xAs/InyGa1â^'yAs quantum wells. Physical Review B, 1996, 54, 10644-10651.	3.2	9
143	Many-particle effects in Be-Î´-dopedGaAs/AlxGa1â^'xAsquantum wells. Physical Review B, 1998, 58, 1424-1435.	3.2	9
144	Photoluminescence studies of individual and few GaSb/GaAs quantum rings. AIP Advances, 2014, 4, .	1.3	9

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145	Height stabilization of GaSb/GaAs quantum dots by Al-rich capping. APL Materials, 2014, 2, 096111.	5.1	9
146	Geometric and compositional influences on spin-orbit induced circulating currents in nanostructures. Physical Review B, 2014, 90, .	3.2	9
147	Active tuning of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math> -tensor in InGaAs/GaAs quantum dots via strain. Physical Review B, 2019, 99, .	3.2	9
148	Electronic structure of a Si Î´-doped layer in a GaAs/AlxGa1âˆ’xAs/GaAs quantum barrier. Physical Review B, 1996, 54, 7996-8004.	3.2	8
149	Annealing of InGaAlAs digital alloy studied with scanning-tunneling microscopy and filled-states topography. Applied Physics Letters, 2003, 82, 1191-1193.	3.3	8
150	Electroluminescence spectra of an STM-tip-induced quantum dot. Physical Review B, 2003, 68, .	3.2	8
151	Cross-sectional scanning tunneling microscopy study on IIâ€“VI multilayer structures. Applied Physics Letters, 2007, 91, .	3.3	8
152	Challenges in cross-sectional scanning tunneling microscopy on semiconductors. Semiconductor Science and Technology, 2011, 26, 064001.	2.0	8
153	Laser and voltage manipulation of bistable Si dopants in the GaAs (110) surface. Physical Review B, 2013, 87, .	3.2	8
154	Spatially resolved electronic structure of an isovalent nitrogen center in GaAs. Physical Review B, 2017, 96, .	3.2	8
155	Enhancement of spin-dependent hole delocalization in degenerate asymmetric double quantum wells. Physical Review B, 1996, 53, 10000-10007.	3.2	7
156	Aharonov-Bohm oscillations in the magnetic moment of multielectron randomly doped semiconductor cylindrical core-shell nanowires. Physical Review B, 2013, 87, .	3.2	7
157	Exchange interaction inp-typeGaAs/AlxGa1âˆ’xAsheterostructures studied by magnetotransport. Physical Review B, 1998, 57, 6629-6635.	3.2	6
158	Correlation lengths in stacked InAs quantum dot systems studied by cross-sectional scanning tunnelling microscopy. Nanotechnology, 2007, 18, 145403.	2.6	6
159	Nanoscale Potential Fluctuations in (GaMn)As/GaAs Heterostructures: From Individual Ions to Charge Clusters and Electrostatic Quantum Dots. Nano Letters, 2010, 10, 4874-4879.	9.1	6
160	Shape and size control of InAs/InP (113)B quantum dots by Sb deposition during the capping procedure. Nanotechnology, 2011, 22, 055703.	2.6	6
161	Self-Assembly of GaAs Quantum Wires Grown on (311)A Substrates by Droplet Epitaxy. Applied Physics Express, 2011, 4, 055501.	2.4	6
162	Structural and electronic properties of isovalent boron atoms in GaAs. Journal of Applied Physics, 2018, 123, 161589.	2.5	6

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163	Control of Morphology and Substrate Etching in InAs/InP Droplet Epitaxy Quantum Dots for Single and Entangled Photon Emitters. ACS Applied Nano Materials, 2022, 5, 8070-8079.	5.0	6
164	Sn delta-doping in GaAs. Semiconductor Science and Technology, 1999, 14, 1034-1041.	2.0	5
165	Lorentzian noise in the two-dimensional electron gas of AlxGa1â^'xAs/GaAs quantum wells. Journal of Applied Physics, 1999, 86, 6206-6212.	2.5	5
166	Modeling of the Magnetization Behavior of Realistic Self-Organized InAs/GaAs Quantum Craters as Observed with Cross-Sectional STM. AIP Conference Proceedings, 2005, , .	0.4	5
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